NSR-4425i

[6 inch Reticle Type, 44 mm sq. Field]

Standard Acceptance DATA.

CND SEMI CO., LTD

NSR-4425i [6 inch Reticle Type, 44 mm sq. Field]
Standard Acceptance Test Results

NSR Serial No.: 1107108 Customer's Machine ID: 1107108

Acceptance Test Completion Date: 2010-07-27

Inspected by: LIM JEONG HOON

No.	Item	Specification	Results
1	Wafer Flatness.	Max – Min ≤ 3 μm	100720_WFLAT.WFLT 2.52 μm
2	Lens Distortion	≤ ± 0.120 μm	100723_DIS.MESR(MainV) min max X : -0.052 ~ 0.053 μm Y : -0.041 ~ 0.056 μm
3	Maximum Exposure Area.	44.00 mm (hor.) X 54.00 mm (ver.)	By Microscope O.K
4	Reticle Blind Setting Accuracy.	+0.4 mm to +0.8 mm	By Microscope min max X: 0.5 ~ 0.7 mm Y: 0.6 ~ 0.65 mm
5	Exposure Power.	≥ 230 mW/cm^2	100724_LAMP.LAMP 229.9 mW/cm^2
6	Integrated Exposure Control Accuracy.	100 , 200 , 400 , 800 mJ/cm^2 ≤ ± 1.0 %	By Nikon Irradiance Meter - 0.2 ~ 0.0 %
7	Illumination Uniformity.	≤ ± 2.0 %	100724_LAMP.LAMP 1.561 %
8	Reticle Rotation.	| M | + 3σ ≤ 0.040 μm	100722_3_RR05.MESR AVE : 0.002 μm 3σ : 0.005 μm 0.007 μm

No.	Item	Specification	Results
9	Alignment Accuracy. (LSA-EGA) Chip center and 4 corners measurement.	| M | + 3σ ≤ 0.150 µm	100724_REG05_LSA.MESR X : 0.103 µm Y : 0.099 µm
	(FIA-EGA) Chip center and 4 corners measurement.	| M | + 3σ ≤ 0.150 µm	100724_REG05_FIA.MESR X : 0.054 µm Y : 0.052 µm
10	Array Orthogonality.	≤ ± 0.48 µrad	By EGA Result. ORTM : -0.3 µrad ORT90M : 0.249 µrad -0.025 µrad
11	Stepping Precision.	3σ ≤ 80 µm	100724_STEP.MESR X 1 : 0.039 µm X 2 : 0.041 µm Y 1 : 0.040 µm Y 2 : 0.066 µm
12	Wafer Pre-alignment Repeatability	3σ ≤ 25 µm	100726_30.WRP(MainV) X : 8.2 µm Y : 6.8 µm Y-θ : 8.1 µm
13	Operational Test (1) Wafer system	Success rate : ≥ 99 %	100 %
	(2) Reticle system	Success rate : 100 %	100 %